# DNSemi

## **General Purpose Transistor**

### NPN Silicon

### MMBT3904L, SMMBT3904L

#### Features

- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and **PPAP** Capable

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V <sub>CEO</sub>	40	Vdc
Collector – Base Voltage	V <sub>CBO</sub>	60	Vdc
Emitter – Base Voltage	V <sub>EBO</sub>	6.0	Vdc
Collector Current – Continuous	۱ <sub>C</sub>	200	mAdc
Collector Current – Peak (Note 3)	I <sub>CM</sub>	900	mAdc

#### THERMAL CHARACTERISTICS

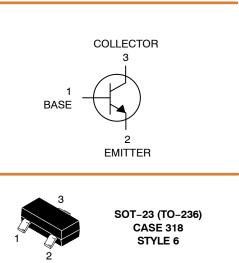
Characteristic	Symbol	Max	Unit
Total Device Dissipation FR- 5 Board (Note 1) @T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) @T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR-5 =  $1.0 \times 0.75 \times 0.062$  in.

2. Alumina =  $0.4 \times 0.3 \times 0.024$  in. 99.5% alumina.

3. Reference SOA curve.



#### MARKING DIAGRAM



1AM = Specific Device Code Μ = Date Code\*

= Pb-Free Package

. (Note: Microdot may be in either location)

\*Date Code orientation and/or overbar may vary depending upon manufacturing location.

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MMBT3904LT1G	SOT-23	3000 / Tape &
SMMBT3904LT1G	i (Pb-Free)	Reel
MMBT3904LT3G	SOT-23	10,000 / Tape &
SMMBT3904LT3G	(Pb-Free)	Reel

+For information on tape and reel specifications. including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

#### **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS			-	
Collector – Emitter Breakdown Voltage ( $I_C = 1.0 \text{ mAdc}, I_B = 0$ )	V <sub>(BR)CEO</sub>	40	-	Vdc
Collector – Base Breakdown Voltage ( $I_C = 10 \ \mu Adc, I_E = 0$ )	V <sub>(BR)CBO</sub>	60	-	Vdc
Emitter – Base Breakdown Voltage ( $I_E = 10 \ \mu Adc, I_C = 0$ )	V <sub>(BR)EBO</sub>	6.0	-	Vdc
Base Cutoff Current ( $V_{CE}$ = 30 Vdc, $V_{EB}$ = 3.0 Vdc)	I <sub>BL</sub>	-	50	nAdc
Collector Cutoff Current (V <sub>CE</sub> = 30 Vdc, V <sub>EB</sub> = 3.0 Vdc)	I <sub>CEX</sub>	-	50	nAdc
ON CHARACTERISTICS (Note 4)				

#### **ON CHARACTERISTICS** (Note 4)

DC Current Gain $(I_{C} = 0.1 \text{ mAdc}, V_{CE} = 1.0 \text{ Vdc})$ $(I_{C} = 1.0 \text{ mAdc}, V_{CE} = 1.0 \text{ Vdc})$ $(I_{C} = 10 \text{ mAdc}, V_{CE} = 1.0 \text{ Vdc})$ $(I_{C} = 50 \text{ mAdc}, V_{CE} = 1.0 \text{ Vdc})$ $(I_{C} = 100 \text{ mAdc}, V_{CE} = 1.0 \text{ Vdc})$	H <sub>FE</sub>	40 70 100 60 30	- - 300 -	_
$\begin{tabular}{lllllllllllllllllllllllllllllllllll$	V <sub>CE(sat)</sub>		0.2 0.3	Vdc
Base – Emitter Saturation Voltage ( $I_C = 10 \text{ mAdc}$ , $I_B = 1.0 \text{ mAdc}$ ) ( $I_C = 50 \text{ mAdc}$ , $I_B = 5.0 \text{ mAdc}$ )	V <sub>BE(sat)</sub>	0.65 -	0.85 0.95	Vdc

#### SMALL-SIGNAL CHARACTERISTICS

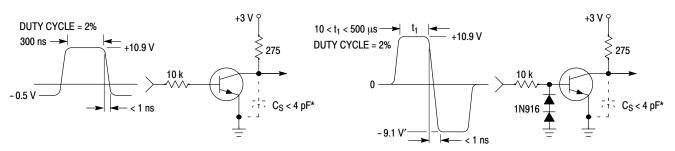
Current – Gain – Bandwidth Product ( $I_C$ = 10 mAdc, $V_{CE}$ = 20 Vdc, f = 100 MHz)	f <sub>T</sub>	300	-	MHz
Output Capacitance ( $V_{CB}$ = 5.0 Vdc, $I_E$ = 0, f = 1.0 MHz)	C <sub>obo</sub>	-	4.0	pF
Input Capacitance (V <sub>EB</sub> = 0.5 Vdc, $I_C$ = 0, f = 1.0 MHz)	C <sub>ibo</sub>	-	8.0	pF
Input Impedance (V <sub>CE</sub> = 10 Vdc, I <sub>C</sub> = 1.0 mAdc, f = 1.0 kHz)	h <sub>ie</sub>	1.0	10	kΩ
Voltage Feedback Ratio ( $V_{CE}$ = 10 Vdc, $I_{C}$ = 1.0 mAdc, f = 1.0 kHz)	h <sub>re</sub>	0.5	8.0	X 10 <sup>-4</sup>
Small – Signal Current Gain ( $V_{CE}$ = 10 Vdc, $I_{C}$ = 1.0 mAdc, f = 1.0 kHz)	h <sub>fe</sub>	100	400	-
Output Admittance ( $V_{CE}$ = 10 Vdc, $I_{C}$ = 1.0 mAdc, f = 1.0 kHz)	h <sub>oe</sub>	1.0	40	μmhos
Noise Figure (V <sub>CE</sub> = 5.0 Vdc, I <sub>C</sub> = 100 $\mu$ Adc, R <sub>S</sub> = 1.0 k ohms, f = 1.0 kHz)	NF	-	5.0	dB

#### SWITCHING CHARACTERISTICS

Delay Time	(V <sub>CC</sub> = 3.0 Vdc, V <sub>BE</sub> = -0.5 Vdc,	t <sub>d</sub>	-	35	20
Rise Time	$I_{\rm C} = 10 \text{ mAdc}, I_{\rm B1} = 1.0 \text{ mAdc})$	tr	-	35	ns
Storage Time	(V <sub>CC</sub> = 3.0 Vdc,	t <sub>s</sub>	-	200	20
Fall Time	$I_{\rm C}$ = 10 mAdc, $I_{\rm B1}$ = $I_{\rm B2}$ = 1.0 mAdc)	t <sub>f</sub>	-	50	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

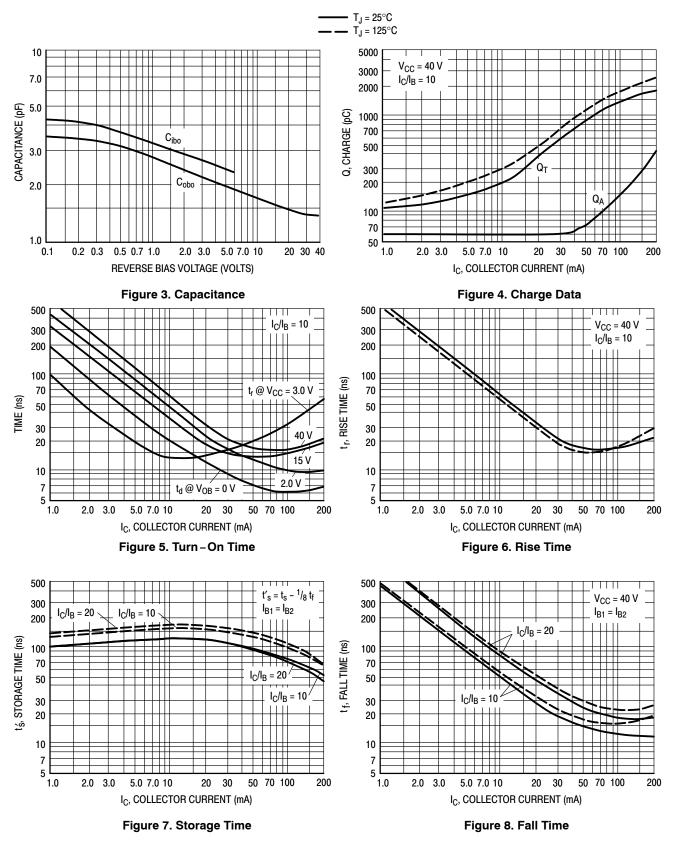
4. Pulse Test: Pulse Width  $\leq$  300 µs, Duty Cycle  $\leq$  2.0%.



\* Total shunt capacitance of test jig and connectors

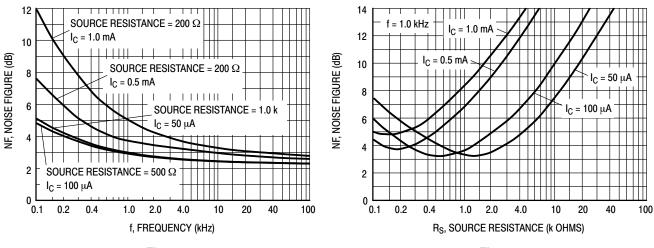
Figure 1. Delay and Rise Time Equivalent Test Circuit Figure 2. Storage and Fall Time Equivalent Test Circuit

#### **TYPICAL TRANSIENT CHARACTERISTICS**



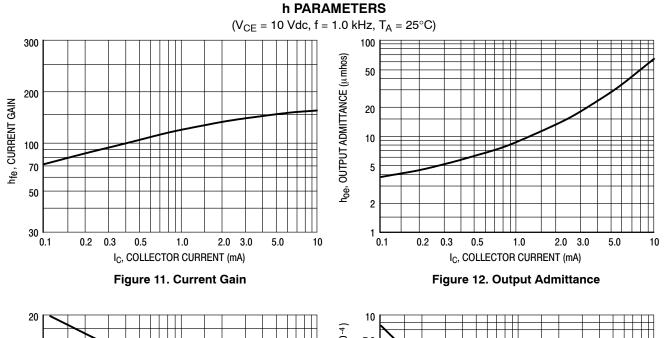
#### TYPICAL AUDIO SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE VARIATIONS

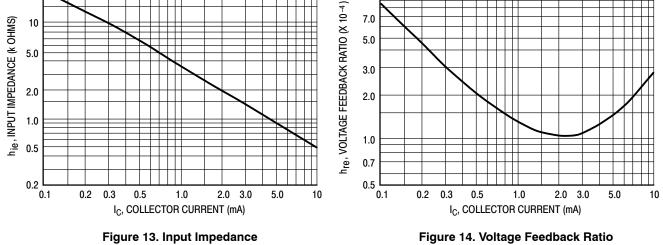
(V<sub>CE</sub> = 5.0 Vdc,  $T_A$  = 25°C, Bandwidth = 1.0 Hz)











#### **TYPICAL STATIC CHARACTERISTICS**

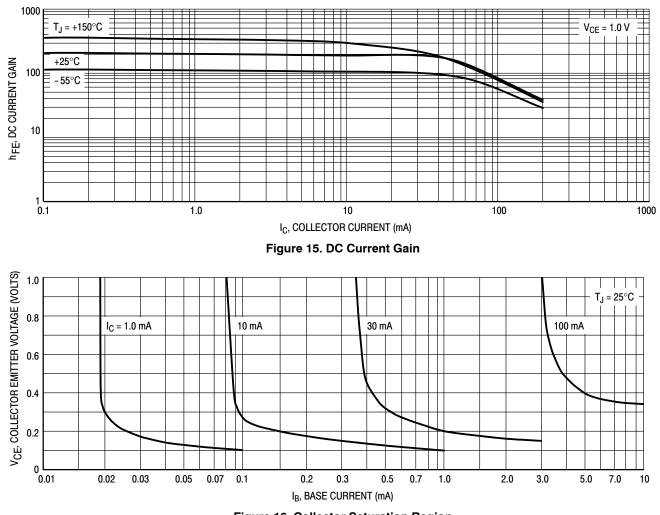
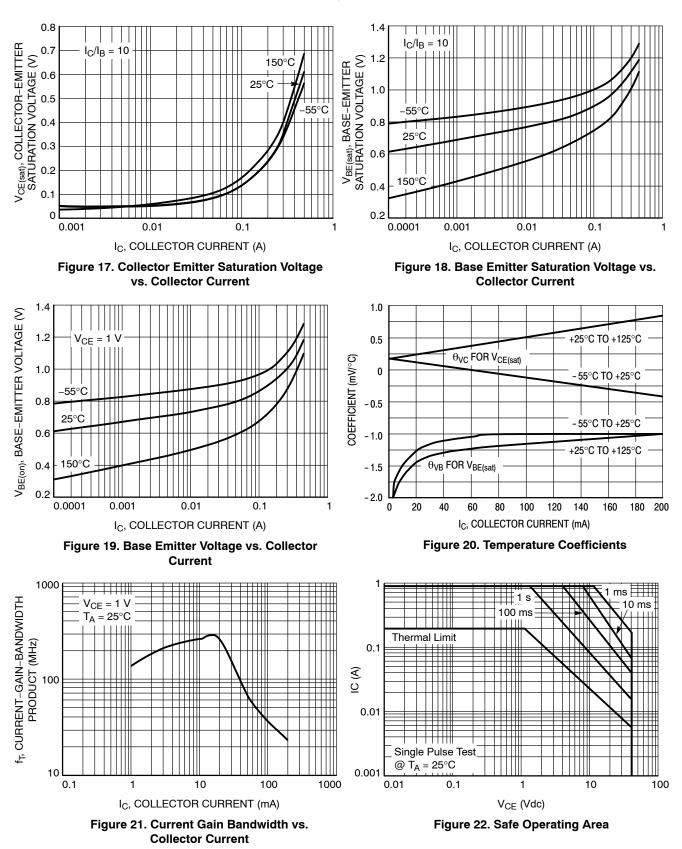


Figure 16. Collector Saturation Region







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